## High Accuracy Hall-Effect-Based Current Sensor with 265 μΩ Integrated Conductor

#### **FEATURES AND BENEFITS**

- AEC-Q100 automotive qualification pending
- Differential Hall sensing rejects common-mode fields
- UL60950-1 (ed. 2) and UL 62368 (ed. 1) certification
  - $\Box$  Dielectric Strength Voltage = 5 kV<sub>RMS</sub>
  - $\hfill \Box$  Basic Isolation Working Voltage = 1140  $V_{RMS}$  and 1600  $V_{DC}$
  - $\hfill\Box$  Reinforced Isolation Working Voltage = 757  $V_{RMS}$  and 813  $V_{DC}$
- Filter pin allows user to filter output for improved resolution (noise) at lower bandwidth
- 265  $\mu\Omega$  primary conductor resistance for low power loss and high continuous current withstand capability
- Custom SOIC16W-like package with 2.5× thicker leads for reduced resistance and slightly oversized body to achieve > 8.2 mm of creepage/clearance
- 3.3 or 5 V single supply operation
- Output voltage proportional to AC or DC current
- Factory-trimmed sensitivity and quiescent output voltage for improved accuracy
- Chopper stabilization results in extremely stable quiescent output voltage
- Nearly zero magnetic hysteresis
- · Ratiometric output from supply voltage





## PACKAGE: 16-pin SOICW (suffix MC)



Not to scale

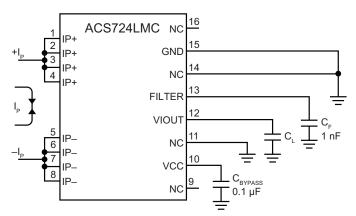
#### DESCRIPTION

The Allegro™ ACS724/5LMC current sensor IC is an economical and precise solution for AC or DC current sensing in industrial, and communication systems. The small package is ideal for space-constrained applications while also saving costs due to reduced board area. Typical applications include solar inverters, DC/DC, electric vehicles on-board chargers, motor control, load detection and management, switched-mode power supplies, and overcurrent fault protection.

The device consists of a precise, low-offset, linear Hall sensor circuit with a copper conduction path located near the surface of the die. Applied current flowing through this copper conduction path generates a magnetic field which is sensed by the integrated Hall IC and converted into a proportional voltage. The current is sensed differentially in order to reject common-mode fields, improving accuracy in magnetically noisy environments. The inherent device accuracy is optimized through the close proximity of the magnetic field to the Hall transducer. A precise, proportional voltage is provided by the low-offset, chopper-stabilized BiCMOS Hall IC, which includes Allegro's patented digital temperature compensation, resulting in extremely accurate performance over temperature. The output of the device has a positive slope when an increasing current flows through the primary copper conduction path (from pins 1 through 4, to pins 5 through 8), which is the path used for current sensing. The internal resistance of this conductive path is 265  $\mu\Omega$  typical, providing low power loss.

The terminals of the conductive path are electrically isolated from the sensor leads (pins 9 through 16). This allows the ACS724/5LMC current sensor IC to be used in high-side current sense applications without the use of high-side differential amplifiers or other costly isolation techniques.

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The ACS724/5LMC outputs an analog signal,  $V_{\rm IOUT}$ , that changes proportionally with the bidirectional AC or DC primary sensed current,  $I_{\rm p}$ , within the specified measurement range.

The FILTER pin can be used to decrease the bandwidth in order to optimize the noise performance.

**Typical Application** 

## High Accuracy Hall-Effect-Based Current Sensor with 265 μΩ Integrated Conductor

### **DESCRIPTION** (continued)

The ACS724/5LMC is provided in a custom SOIC16-like surface mount package. The pin pitch is the same as a standard SOIC16 but the lead-frame is 2.5 times as thick to reduce the resistance. The package body is also sized to achieve greater than 8.2 mm of creepage/clearance. The leadframe is plated with 100% matte tin, which is compatible with standard lead (Pb) free printed circuit board assembly processes. Internally, the device is Pb-free. The device is fully calibrated prior to shipment from the factory.

#### **SELECTION GUIDE**

Part Number	I <sub>PR</sub> (A)	Sens(Typ) (mV/A)	Nominal V <sub>CC</sub> (V)	T <sub>A</sub> (°C)	Packing <sup>[1]</sup>
ACS724LMCTR-20AB-T	±20	100	5		
ACS724LMCTR-30AB-T	±30	66	5	-40 to 150	Tana and Book 1000 pieces per real
ACS724LMCTR-65AB-T	±65	30.75	5		Tape and Reel, 1000 pieces per reel
ACS725LMCTR-20AB-T	±20	66	3.3		

<sup>[1]</sup> Contact Allegro for additional packing options.





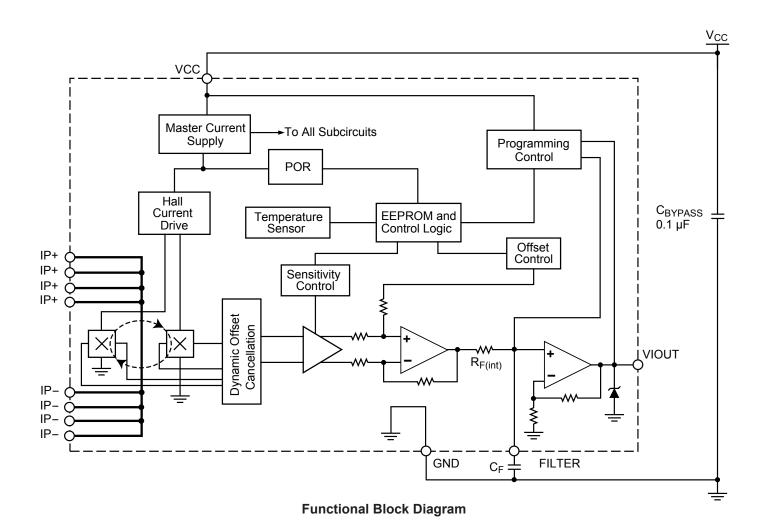
### **SPECIFICATIONS**

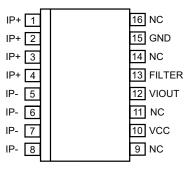
#### **ABSOLUTE MAXIMUM RATINGS**

Characteristic	Symbol	Notes	Rating	Units
Supply Voltage	V <sub>CC</sub>		6	V
Reverse Supply Voltage	V <sub>RCC</sub>		-0.1	V
Output Voltage	V <sub>IOUT,</sub> V <sub>FILTER</sub>	VIOUT and FILTER pins	V <sub>CC</sub> + 0.5	V
Reverse Output Voltage	V <sub>RIOUT</sub> , V <sub>RFILTER</sub>	VIOUT and FILTER pins	-0.1	V
Operating Ambient Temperature	T <sub>A</sub>	Range L	-40 to 150	°C
Junction Temperature	T <sub>J</sub> (max)		165	°C
Storage Temperature	T <sub>stg</sub>		-65 to 165	°C

#### **ISOLATION CHARACTERISTICS**

Characteristic	Symbol	Notes	Rating	Unit
Dielectric Surge Strength Test Voltage	V <sub>SURGE</sub>	Tested ±5 pulses at 2/minute in compliance to IEC 61000-4-5 1.2 µs (rise) / 50 µs (width).	13	kV
Dielectric Strength Test Voltage	V <sub>ISO</sub>	Agency type-tested for 60 seconds per UL 60950-1 (edition 2) and UL 62368 (edition 1). Production tested at 3125 V <sub>RMS</sub> for 1 second, in accordance with UL 60950-1 (edition 2) and UL 62368 (edition 1).	5000	$V_{RMS}$
Marking Valtage for Desig legistion		Maximum approved working voltage for basic (single) isolation	1600	V <sub>PK</sub> or V <sub>DC</sub>
Working Voltage for Basic Isolation	V <sub>WVBI</sub>	according to UL 60950-1 (edition 2) and UL 62368 (edition 1).	1140	V <sub>RMS</sub>
Marking Valtage for Deinforced legistics	V	Maximum approved working voltage for reinforced isolation	813	V <sub>PK</sub> or V <sub>DC</sub>
Working Voltage for Reinforced Isolation	V <sub>WVRI</sub>	according to UL 60950-1 (edition 2) and UL 62368 (edition 1).	757	V <sub>RMS</sub>
Clearance	D <sub>cl</sub>	Minimum distance through air from IP leads to signal leads.	8.2	mm
Creepage	D <sub>cr</sub>	Minimum distance along package body from IP leads to signal leads	8.2	mm
Distance Through Insulation	DTI	Minimum internal distance through insulation	70	μm
Comparative Tracking Index	CTI	Material Group II	400 to 599	V





**Pinout Diagram** 

#### **Terminal List Table**

Number	Name	Description
1, 2, 3, 4	IP+	Terminals for current being sensed; fused internally
5, 6, 7, 8	IP-	Terminals for current being sensed; fused internally
9, 16	NC	No internal connection; recommended to be left unconnected in order to maintain high creepage
10	VCC	Device power supply terminal
11, 14	NC	No internal connection; recommened to connect to GND for the best ESD performance
12	VIOUT	Analog output signal
13	FILTER	Terminal for external capacitor that sets bandwidth
15	GND	Signal ground terminal

## High Accuracy Hall-Effect-Based Current Sensor with 265 μΩ Integrated Conductor

## COMMON ELECTRICAL CHARACTERISTICS [1]: Valid through the full range of $T_A = -40^{\circ}\text{C}$ to 150°C and $V_{CC} = V_{CC}(typ)$ , unless otherwise specified

Characteristic	Symbol	Test Condition	s	Min.	Тур.	Max.	Units
O	.,	ACS724		4.5	5	5	V
Supply Voltage	V <sub>CC</sub>	ACS725		3	3.3	3.6	V
Supply Current	I <sub>CC</sub>				12	14	mA
Output Capacitive Load	C <sub>L</sub>	VIOUT to GND		_	_	10	nF
Output Resistive Load	R <sub>L</sub>	VIOUT to GND		4.7	_	_	kΩ
Primary Conductor Resistance	R <sub>IP</sub>	T <sub>A</sub> = 25°C		_	265	_	μΩ
Internal Filter Resistance [2]	R <sub>R(INT)</sub>			-	1.7	_	kΩ
Common Mode Field Rejection Ratio	CMFRR	Uniform External Magnetic F	Field	_	2.21	_	mA/G
Primary Hall Coupling Factor	G1	T <sub>A</sub> = 25°C		_	3.5	_	G/A
Secondary Hall Coupling Factor	G2	T <sub>A</sub> = 25°C		_	-0.5	_	G/A
Differential Coupling Factor	G1-G2	T <sub>A</sub> = 25°C		_	4	_	G/A
Rise Time	t <sub>r</sub>	$I_P = I_P(max), T_A = 25^{\circ}C, C_L = 10^{\circ}$	= 1 nF	_	3	_	μs
Propagation Delay	t <sub>pd</sub>	$I_P = I_P(max), T_A = 25^{\circ}C, C_L = 10^{\circ}$	= 1 nF	_	2	_	μs
Response Time	t <sub>RESPONSE</sub>	$I_P = I_P(max), T_A = 25^{\circ}C, C_L =$	= 1 nF	_	4	_	μs
Internal Bandwidth	BW	small signal –3 dB, CL = 1nl	F	_	120	_	kHz
Noise Density		Input-referenced noise	V <sub>CC</sub> = 5 V	-	400	_	μA <sub>RMS</sub> / √Hz
Noise Density	I <sub>ND</sub>	density; T <sub>A</sub> = 25°C, C <sub>L</sub> = 1 nF	V <sub>CC</sub> = 3.3 V	_	550	_	μA <sub>RMS</sub> / √Hz
Noise	I <sub>N</sub>	Input-referenced noise; C <sub>F</sub> = 4.7 nF, C <sub>L</sub> = 1 nF,	V <sub>CC</sub> = 5 V	_	70	-	mA <sub>RMS</sub>
	-14	BW = 18 kHz, T <sub>A</sub> = 25°C	V <sub>CC</sub> = 3.3 V	_	80	_	mA <sub>RMS</sub>
Nonlinearity	_	Through full range of l	V <sub>CC</sub> = 5 V	-1	_	1	%
Nonlinearity	E <sub>LIN</sub>	Through full range of I <sub>P</sub>	V <sub>CC</sub> = 3.3 V	-1.5	_	1.5	%
	\/	D = 4.7k0 T = 25°C	V <sub>CC</sub> = 5 V	$V_{CC} - 0.5$	_	_	V
Caturation Valtage [3]	V <sub>OH</sub>	$R_L = 4.7 \text{ k}\Omega, T_A = 25^{\circ}\text{C}$	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> - 0.3	_	_	V
Saturation Voltage [3]	\/	$R_1 = 4.7 \text{ k}\Omega, T_A = 25^{\circ}\text{C}$	V <sub>CC</sub> = 5 V	_	_	0.5	V
	V <sub>OL</sub>	K <sub>L</sub> - 4.7 KΩ, 1 <sub>A</sub> - 25 C	V <sub>CC</sub> = 3.3 V	_	_	0.3	V
Power-On Time	t <sub>PO</sub>	Output reaches 90% of steady-state level, $T_A = 25^{\circ}C$ , $I_P = I_{PR}(max)$ applied		-	80	-	μs
Shorted Output to Ground Current	I <sub>SC(GND)</sub>	T <sub>A</sub> = 25°C		-	3	_	mA
Shorted Output to V <sub>CC</sub> Current	I <sub>SC(VCC)</sub>	T <sub>A</sub> = 25°C		_	45	_	mA

<sup>[1]</sup> Device may be operated at higher primary current levels, I<sub>P</sub>, ambient temperatures, T<sub>A</sub>, and internal leadframe temperatures, provided the Maximum Junction Temperature, T<sub>J</sub>(max), is not exceeded.

## High Accuracy Hall-Effect-Based Current Sensor with 265 μΩ Integrated Conductor

#### ACS724LMCTR-20AB PERFORMANCE CHARACTERISTICS: $T_A = -40$ °C to 150°C, $V_{CC} = 5$ V, unless otherwise specified

			, 66			
Characteristic	Symbol	Symbol Test Conditions		Typ. [1]	Max.	Units
NOMINAL PERFORMANCE						
Current Sensing Range	I <sub>PR</sub>		-20	_	20	Α
Sensitivity	Sens		_	100 × V <sub>CC</sub> / 5	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	_	V <sub>CC</sub> × 0.5	_	V
ACCURACY PERFORMANO	E					
T-1-1 O-1-1 F [2]	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2.5	±1.3	2.5	%
Total Output Error [2]	E <sub>TOT</sub>	$I_P = I_{PR(max)}$ , $T_A = -40$ °C to 25°C	-2.5	±1.5	2.5	%
TOTAL OUTPUT ERROR CO	OMPONENT:	S [3]				
Compitibility Fores	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2	±1.2	2	%
Sensitivity Error	E <sub>SENS</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-2	±1.4	2	%
Officet Valtage [4]		I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 150°C	-15	±8.8	15	mV
Offset Voltage [4]	V <sub>OE</sub>	I <sub>P</sub> = 0 A, T <sub>A</sub> = -40°C to 25°C	-15	±8.8	15	mV
LIFETIME DRIFT CHARACT	ERISTICS [5	1				
Total Output Error Including	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-3	±1.6	3	%
Lifetime Drift [6]	E <sub>TOT(DRIFT)</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4.1	±1.5	4.1	%
Sensitivity Error Including	_	$I_{\rm B} = I_{\rm BB(max)}$ , $T_{\rm A} = 25^{\circ}{\rm C}$ to 150°C	-2.7	±1.2	2.7	%
Lifetime Drift [7]	E <sub>SENS(DRIFT)</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4.1	±1.4	4.1	%

<sup>[1]</sup> Typical values with ± are 3 sigma values, except for lifetime drift characteristics. The typical lifetime drift characteristics are the average values, including drift, from the worst case stress, observed during qualification.

<sup>[2]</sup> Percentage of  $I_P$ , with  $I_P = I_{PR(max)}$ , output filtered.

<sup>[3]</sup> A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output error specification.

<sup>[4]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 9 mV and 5 mV respectively.

<sup>[5]</sup> Pending qualification completion.

<sup>[6]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2% and 2% respectively.

<sup>[7]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2.1% and 1.5% respectively.

## **High Accuracy Hall-Effect-Based Current Sensor** with 265 $\mu\Omega$ Integrated Conductor

#### ACS724LMCTR-30AB PERFORMANCE CHARACTERISTICS: $T_A = -40^{\circ}$ C to 150°C, $V_{CC} = 5$ V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Units
NOMINAL PERFORMANCE						
Current Sensing Range	I <sub>PR</sub>		-30	_	30	А
Sensitivity	Sens		_	66 × V <sub>CC</sub> / 5	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	_	V <sub>CC</sub> × 0.5	_	V
ACCURACY PERFORMANO						
Total Outrot Francis	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2.5	±1.3	2.5	%
Total Output Error [2]	E <sub>TOT</sub>	$I_P = I_{PR(max)}$ , $T_A = -40^{\circ}C$ to 25°C	-2.5	±1.5	2.5	%
TOTAL OUTPUT ERROR CO	OMPONENT:	S [3]				
Consitivity Fran	E <sub>SENS</sub>	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2	±1.2	2	%
Sensitivity Error		$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-2	±1.4	2	%
Officet Voltage [/]	\/	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 150°C	-15	±8.8	15	mV
Offset Voltage [4]	V <sub>OE</sub>	$I_P = 0 \text{ A}, T_A = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	-15	±8.8	15	mV
LIFETIME DRIFT CHARACT	ERISTICS [5	1				
Total Output Error Including	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-3	±1.6	3	%
Lifetime Drift [6]	E <sub>TOT(DRIFT)</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4.1	±1.5	4.1	%
Sensitivity Error Including	F	$I_{\rm D} = I_{\rm DB (max)}$ , $T_{\rm A} = 25^{\circ}{\rm C}$ to 150°C	-2.7	±1.2	2.7	%
Lifetime Drift [7]	E <sub>SENS(DRIFT)</sub>	$I_P = I_{PR(max)}$ , $T_A = -40$ °C to 25°C	-4.1	±1.4	4.1	%

<sup>[1]</sup> Typical values with ± are 3 sigma values, except for lifetime drift characteristics. The typical lifetime drift characteristics are the average values, including drift, from the worst case stress, observed during qualification.



<sup>[2]</sup> Percentage of I<sub>P,</sub> with I<sub>P</sub> = I<sub>PR(max)</sub>, output filtered.
[3] A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output error specification.

<sup>[4]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 9 mV and 5 mV respectively.

<sup>[5]</sup> Pending qualification completion.

<sup>[6]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2% and 2% respectively.

<sup>[7]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2.1% and 1.5% respectively.

## **High Accuracy Hall-Effect-Based Current Sensor** with 265 $\mu\Omega$ Integrated Conductor

#### ACS724LMCTR-65AB PERFORMANCE CHARACTERISTICS: $T_A = -40$ °C to 150°C, $V_{CC} = 5$ V, unless otherwise specified

		~				
Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Units
NOMINAL PERFORMANCE						
Current Sensing Range	I <sub>PR</sub>		-65	_	65	А
Sensitivity	Sens		_	30.75 × V <sub>CC</sub> / 5	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	_	V <sub>CC</sub> × 0.5	_	V
ACCURACY PERFORMANO						
Total Outrot Face [2]	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2.5	±1.3	2.5	%
Total Output Error [2]	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-2.5	±1.5	2.5	%
TOTAL OUTPUT ERROR CO	OMPONENT:	S [3]				
Consitivity Fran	E <sub>SENS</sub>	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2	±1.2	2	%
Sensitivity Error		$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-2	±1.4	2	%
Off at 1/alta a [/]		I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 150°C	-15	±8.8	15	mV
Offset Voltage [4]	V <sub>OE</sub>	$I_P = 0 \text{ A}, T_A = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	-15	±8.8	15	mV
LIFETIME DRIFT CHARACT	ERISTICS [5	1				
Total Output Error Including	_	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-3	±1.6	3	%
Lifetime Drift [6]	E <sub>TOT(DRIFT)</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4.1	±1.5	4.1	%
Sensitivity Error Including	F	$I_{\rm B} = I_{\rm BB(max)}$ , $T_{\rm A} = 25^{\circ}{\rm C}$ to 150°C	-2.7	±1.2	2.7	%
Lifetime Drift [7]	E <sub>SENS(DRIFT)</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-4.1	±1.4	4.1	%

<sup>[1]</sup> Typical values with ± are 3 sigma values, except for lifetime drift characteristics. The typical lifetime drift characteristics are the average values, including drift, from the worst case stress, observed during qualification.

<sup>[2]</sup> Percentage of I<sub>P</sub>, with I<sub>P</sub> = I<sub>PR(max)</sub>, output filtered.
[3] A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output error specification.

<sup>[4]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 9 mV and 5 mV respectively.

<sup>[5]</sup> Pending qualification completion.

<sup>[6]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2% and 2% respectively.

<sup>[7]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2.1% and 1.5% respectively.

## **High Accuracy Hall-Effect-Based Current Sensor** with 265 $\mu\Omega$ Integrated Conductor

ACS725LMCTR-20AB PERFORMANCE CHARACTERISTICS:  $T_A = -40^{\circ}\text{C}$  to 150°C,  $V_{CC} = 3.3 \text{ V}$ , unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Typ. [1]	Max.	Units
NOMINAL PERFORMANCE	•		·			
Current Sensing Range	I <sub>PR</sub>		-20		20	А
Sensitivity	Sens		_	66 × V <sub>CC</sub> / 3.3	_	mV/A
Zero Current Output Voltage	V <sub>IOUT(Q)</sub>	Bidirectional; I <sub>P</sub> = 0 A	-	V <sub>CC</sub> × 0.5	-	V
ACCURACY PERFORMANO						
Tatal Outrant Francis[2]		I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2.5	±1.3	2.5	%
Total Output Error [2]	E <sub>TOT</sub>	$I_P = I_{PR(max)}, T_A = -40^{\circ}C \text{ to } 25^{\circ}C$	-2.5	±1.5	2.5	%
TOTAL OUTPUT ERROR CO	OMPONENT	S [3]				
Concitivity Fran	E <sub>SENS</sub>	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2	±1.2	2	%
Sensitivity Error		$I_P = I_{PR(max)}$ , $T_A = -40$ °C to 25°C	-2	±1.4	2	%
Offeet Voltage [/]	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C to 150°C	-15	±8.8	15	mV
Offset Voltage [4]	V <sub>OE</sub>	$I_P = 0 \text{ A}, T_A = -40^{\circ}\text{C to } 25^{\circ}\text{C}$	-15	±8.8	15	mV
LIFETIME DRIFT CHARACT	TERISTICS [5	1				
Total Output Error Including		I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-3	±1.3	3	%
Lifetime Drift [6]	E <sub>TOT(DRIFT)</sub>	$I_P = I_{PR(max)}$ , $T_A = -40$ °C to 25°C	-4	±1.5	4	%
Sensitivity Error Including	E	I <sub>P</sub> = I <sub>PR(max)</sub> , T <sub>A</sub> = 25°C to 150°C	-2.7	±1.25	2.7	%
Lifetime Drift [7]	E <sub>SENS(DRIFT)</sub>	$I_P = I_{PR(max)}$ , $T_A = -40$ °C to 25°C	-3.8	±1.4	3.8	%

<sup>[1]</sup> Typical values with ± are 3 sigma values, except for lifetime drift characteristics. The typical lifetime drift characteristics are the average values, including drift, from the worst case stress, observed during qualification.

Percentage of I<sub>P</sub>, with I<sub>P</sub> = I<sub>PR(max)</sub>, output filtered.

[3] A single part will not have both the maximum/minimum sensitivity error and maximum/minimum offset voltage, as that would violate the maximum/minimum total output

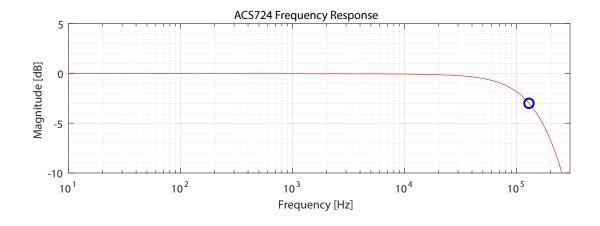
<sup>[4]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 13 mV and 8 mV respectively.

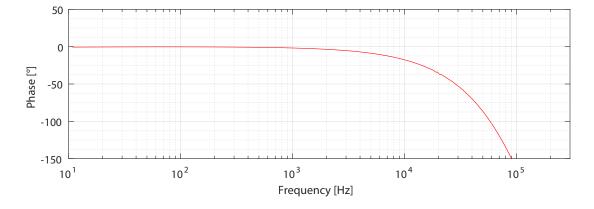
<sup>[5]</sup> Pending qualification completion.

<sup>[6]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2.5% and 2% respectively.

<sup>[7]</sup> All devices remained within the limits during the qualification for 25°C to 150°C and 25°C to -40°C, and the worst observed drift was 2.5% and 1.8% respectively.

## CHARACTERISTIC PERFORMANCE ACS724 TYPICAL FREQUENCY RESPONSE





#### **DEFINITIONS OF ACCURACY CHARACTERISTICS**

### Sensitivity (Sens)

The change in sensor IC output in response to a 1 A change through the primary conductor. The sensitivity is the product of the magnetic coupling factor (G/A) (1 G = 0.1 mT) and the linear IC amplifier gain (mV/G). The linear IC amplifier gain is programmed at the factory to optimize the sensitivity (mV/A) for the full-scale current of the device.

## Nonlinearity (E<sub>LIN</sub>)

The nonlinearity is a measure of how linear the output of the sensor IC is over the full current measurement range. The nonlinearity is calculated as:

$$E_{LIN} = \left\{ 1 - \left[ \frac{V_{IOUT}(I_{PR}(\text{max})) - V_{IOUT(Q)}}{2 \times V_{IOUT}(I_{PR}(\text{max})/2) - V_{IOUT(Q)}} \right] \right\} \times 100 \text{ (\%)}$$

where  $V_{IOUT}(I_{PR(max)})$  is the output of the sensor IC with the maximum measurement current flowing through it and  $V_{IOUT}(I_{PR(max)}/2)$  is the output of the sensor IC with half of the maximum measurement current flowing through it.

## Zero Current Output Voltage (V<sub>IOUT(Q)</sub>)

The output of the sensor when the primary current is zero. For a unipolar supply voltage, it nominally remains at  $0.5 \times V_{CC}$  for a bidirectional device and  $0.1 \times V_{CC}$  for a unidirectional device. For example, in the case of a bidirectional output device,  $V_{CC} = 5.0 \ V$  translates into  $V_{IOUT(Q)} = 2.50 \ V$ . Variation in  $V_{IOUT(Q)}$  can be attributed to the resolution of the Allegro linear IC quiescent voltage trim and thermal drift.

## Offset Voltage (V<sub>OE</sub>)

The deviation of the device output from its ideal quiescent value of  $0.5 \times V_{CC}$  (bidirectional) or  $0.1 \times V_{CC}$  (unidirectional) due to nonmagnetic causes. To convert this voltage to amperes, divide by the device sensitivity, Sens.

## **Total Output Error (E<sub>TOT</sub>)**

The difference between the current measurement from the sensor IC and the actual current  $(I_P)$ , relative to the actual current. This is equivalent to the difference between the ideal output voltage and the actual output voltage, divided by the ideal sensitivity, relative to the current flowing through the primary conduction path:

$$E_{\text{TOT}}(I_{\text{P}}) = \frac{V_{\text{IOUT\_ideal}}(I_{\text{P}}) - V_{\text{IOUT}}(I_{\text{P}})}{\text{Sens}_{\text{Ideal}}(I_{\text{P}}) \times I_{\text{P}}} \times 100 \text{ (\%)}$$

The Total Output Error incorporates all sources of error and is a function of  $I_P$ . At relatively high currents,  $E_{TOT}$  will be mostly due to

sensitivity error, and at relatively low currents,  $E_{TOT}$  will be mostly due to Offset Voltage ( $V_{OE}$ ). In fact, at  $I_P \!=\! 0$ ,  $E_{TOT}$  approaches infinity due to the offset. This is illustrated in Figure 1 and Figure 2. Figure 1 shows a distribution of output voltages versus  $I_P$  at  $25^{\circ}C$  and across temperature. Figure 2 shows the corresponding  $E_{TOT}$  versus  $I_P$ .

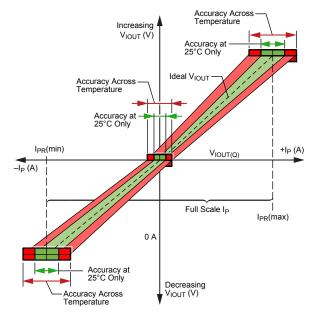


Figure 1: Output Voltage versus Sensed Current

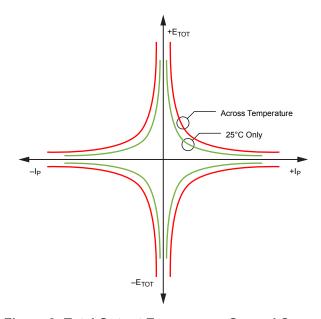


Figure 2: Total Output Error versus Sensed Current

#### **APPLICATION INFORMATION**

### **Estimating Total Error versus Sensed Current**

The Performance Characteristics tables give distribution ( $\pm 3$  sigma) values for Total Error at  $I_{PR(max)}$ ; however, one often wants to know what error to expect at a particular current. This can be estimated by using the distribution data for the components of Total Error, Sensitivity Error, and Offset Voltage. The  $\pm 3$  sigma value for Total Error ( $E_{TOT}$ ) as a function of the sensed current ( $I_P$ ) is estimated as:

$$E_{TOT}(I_p) = \sqrt{E_{SENS}^2 + \left(\frac{100 \times V_{OE}}{Sens \times I_p}\right)^2}$$

Here,  $E_{SENS}$  and  $V_{OE}$  are the  $\pm 3$  sigma values for those error terms. If there is an average sensitivity error or average offset voltage, then the average Total Error is estimated as:

$$E_{\text{TOT}_{AVG}}(I_p) = E_{\text{SENS}_{AVG}} + \frac{100 \times V_{OE_{AVG}}}{Sens \times I_p}$$

The resulting total error will be a sum of  $E_{TOT}$  and  $E_{TOT\_AVG}$ . Using these equations and the 3 sigma distributions for Sensitivity Error and Offset Voltage, the Total Error versus sensed current ( $I_P$ ) is shown here for the ACS724/5LMCTR-20AB. As expected, as one goes towards zero current, the error in percent goes towards infinity due to division by zero.



#### **DEFINITIONS OF DYNAMIC RESPONSE CHARACTERISTICS**

### Power-On Time (t<sub>PO</sub>)

When the supply is ramped to its operating voltage, the device requires a finite time to power its internal components before responding to an input magnetic field.

Power-On Time ( $t_{PO}$ ) is defined as the time it takes for the output voltage to settle within  $\pm 10\%$  of its steady-state value under an applied magnetic field, after the power supply has reached its minimum specified operating voltage ( $V_{CC}(min)$ ) as shown in the chart at right (refer to Figure 3).

## Rise Time (t<sub>r</sub>)

The time interval between: a) when the sensor IC reaches 10% of its full-scale value; and b) when it reaches 90% of its full-scale value (refer to Figure 4). The rise time to a step response is used to derive the bandwidth of the current sensor IC, in which  $f(-3~{\rm dB}) = 0.35/t_{\rm r}$ . Both  $t_{\rm r}$  and  $t_{\rm RESPONSE}$  are detrimentally affected by eddy current losses observed in the conductive IC ground plane.

## Propagation Delay (t<sub>pd</sub>)

The propagation delay is measured as the time interval between: a) when the primary current signal reaches 20% of its final value, and b) when the device reaches 20% of its output corresponding to the applied current (refer to Figure 4).

## Response Time (t<sub>RESPONSE</sub>)

The time interval between: a) when the primary current signal reaches 90% of its final value, and b) when the device reaches 90% of its output corresponding to the applied current (refer to Figure 5).

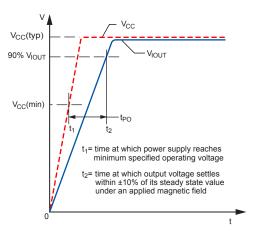


Figure 3: Power-On Time

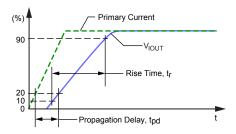


Figure 4: Rise Time and Propagation Delay

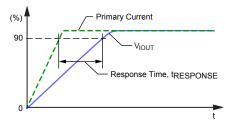


Figure 5: Response Time

#### APPLICATION INFORMATION

### Thermal Rise vs. Primary Current

Self-heating due to the flow of current should be considered during the design of any current sensing system. The sensor, printed circuit board (PCB), and contacts to the PCB will generate heat as current moves through the system.

The thermal response is highly dependent on PCB layout, copper thickness, cooling techniques, and the profile of the injected current. The current profile includes peak current, current "on-time", and duty cycle. While the data presented in this section was collected with direct current (DC), these numbers may be used to approximate thermal response for both AC signals and current pulses.

The plot in Figure 6 shows the measured rise in steady-state die temperature of the ACS724/5MC versus continuous current at an ambient temperature,  $T_A$ , of 25 °C. The thermal offset curves may be directly applied to other values of  $T_A$ . Conversely, Figure 7 shows the maximum continuous current at a given  $T_A$ . Surges beyond the maximum current listed in Figure 7 are allowed given the maximum junction temperature,  $T_{J(MAX)}$  (165°C), is not exceeded.

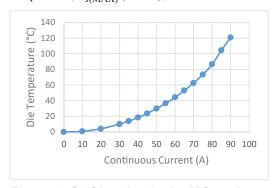


Figure 6: Self-heating in the MC package due to current flow

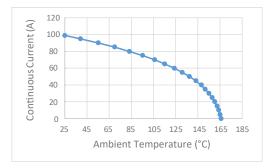


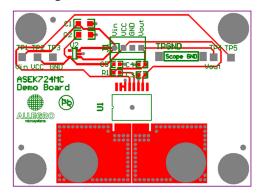
Figure 7: Maximum continuous current at a given TA

The thermal capacity of the ACS724/5LMC should be verified by the end user in the application's specific conditions. The maxi-

mum junction temperature,  $T_{J(MAX)}$ , should not be exceeded. Further information on this application testing is available in the "DC and Transient Current Capability" application note [1] on the Allegro website.

### **ASEK724/5 MC Evaluation Board Layout**

Thermal data shown in Figure 6 and Figure 7 was collected using the ASEK724/5 MC Evaluation Board (TED-0002977). This board includes 1500 mm<sup>2</sup> of 2 oz. (0.1388 mm) copper connected to pins 1 through 4, and to pins 5 through 8, with thermal vias connecting the layers. Top and bottom layers of the PCB are shown below in Figure 8.



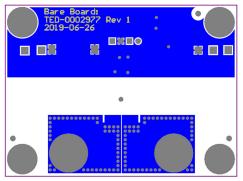


Figure 8: Top and bottom layers for ASEK724/5 MC evaluation board

Gerber files for the ASEK724/5 MC evaluation board are available for download from the Allegro website. See the technical documents section of the ACS724xMC device webpage [2].

[1] http://www.allegromicro.com/en/Design-Center/Technical-Documents/ Hall-Effect-Sensor-IC-Publications/DC-and-Transient-Current-Capability-Fuse-Characteristics.aspx

 $^{[2]}$  https://www.allegromicro.com/en/products/sense/current-sensor-ics/zero-to-fifty-amp-integrated-conductor-sensor-ics/acs724ma



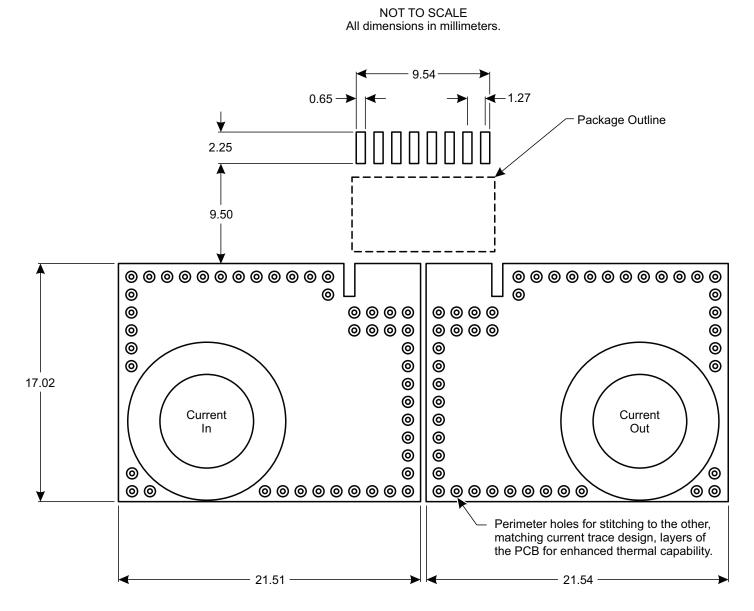


Figure 9: High-Isolation PCB Layout

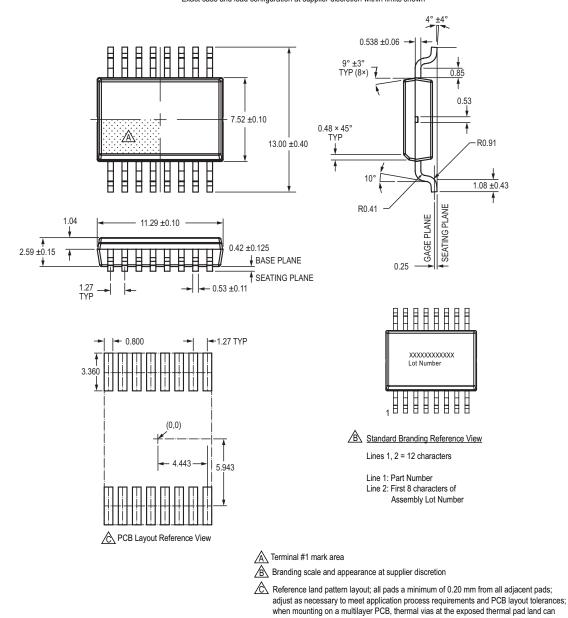
#### PACKAGE OUTLINE DRAWING

#### **PRELIMINARY**

For Reference Only; not for tooling use (reference DWG-0000714, Rev. 1)

Dimensions in millimeters

Dimensions exclusive of mold flash, gate burrs, and dambar protrusions Exact case and lead configuration at supplier discretion within limits shown



improve thermal dissipation (reference EIA/JEDEC Standard JESD51-5)



Figure 10: Package MC, 16-Pin SOICW

## High Accuracy Hall-Effect-Based Current Sensor with 265 $\mu\Omega$ Integrated Conductor

#### **Revision History**

Number	Date	Description
_	February 6, 2020	Initial advance information release
1	March 13, 2020	AEC-Q100 qualification marked pending (page 1); removed ESD ratings and Current Surge Strength (page 3); updated performance characteristics (pages 6-9)
2	June 25, 2020	Updated certification status and added Reinforced Isolation Working Voltage spec (pages 1 and 3)
3	September 25, 2020	Updated CB certificate numbers (page 1)

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